

TMUX112x 5V、低泄漏电流、1:1 (SPST)、2 通道精密开关

1 特性

- 宽电源电压范围：1.08V 至 5.5V
- 低泄漏电流：3pA
- 低电荷注入：-1.5pC
- 低导通电阻：1.9Ω
- -40°C 至 +125°C 工作温度
- [1.8V 逻辑兼容](#)
- [失效防护逻辑](#)
- [轨至轨运行](#)
- [双向信号路径](#)
- 先断后合开关
- ESD 保护 HBM：2000V

2 应用

- 采样保持电路
- 反馈增益开关
- 信号隔离
- 现场变送器
- 可编程逻辑控制器 (PLC)
- 工厂自动化和控制
- 超声波扫描仪
- 患者监护和诊断
- 心电图 (ECG)
- 数据采集系统 (DAQ)
- 半导体测试设备
- 电池测试设备
- 仪表：实验室、分析、便携
- 超声波智能仪表：水表和燃气表
- 光纤网络
- 光学测试设备

3 说明

TMUX1121、TMUX1122 和 TMUX1123 是精密互补金属氧化物半导体 (CMOS) 器件，具有两个独立可选 1:1、单极单投 (SPST) 开关。1.08V 至 5.5V 的宽电源电压工作范围可支持医疗设备到工业系统的大量应用。该器件可在源极 (Sx) 和漏极 (Dx) 引脚上支持从 GND 到 V_{DD} 范围的双向模拟和数字信号。

TMUX1121 的开关可在恰当的逻辑控制输入下通过逻辑 1 打开，而要打开 TMUX1122 中的开关，则需逻辑 0。TMUX1123 的两个通道分别支持逻辑 1 和逻辑 0。TMUX1123 具有先断后合开关，因此该器件可用于交叉点开关应用。

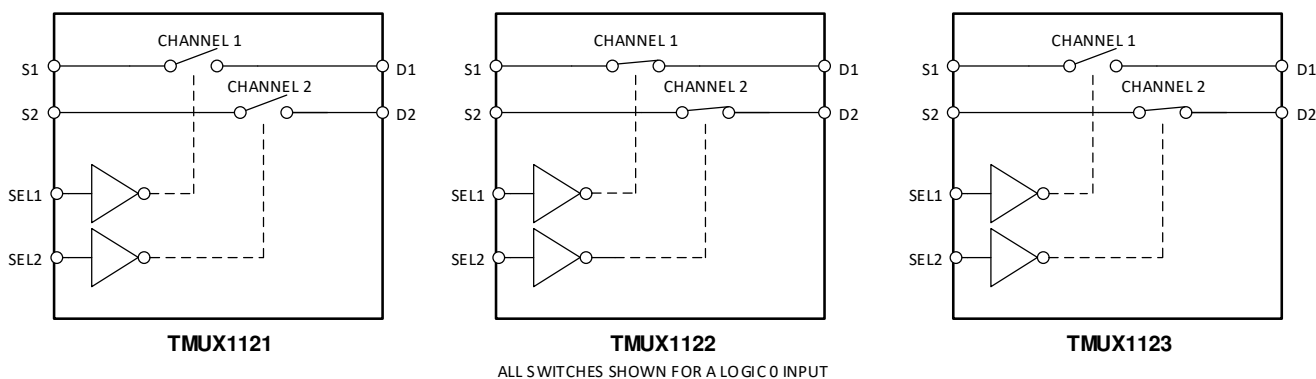
TMUX112x 器件是精密开关和多路复用器器件系列中的一部分。这些器件具有非常低的导通和关断泄漏电流以及较低的电荷注入，因此可用于高精度测量应用。7nA 的低电源电流和小型封装选项使其可用于便携式应用。

器件信息(1)

器件型号	封装	封装尺寸 (标称值)
TMUX1121 TMUX1122 TMUX1123	VSSOP (8) (DGK)	3.00mm x 3.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的封装选项附录。

TMUX112x 方框图



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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Original (August 2019) to Revision A

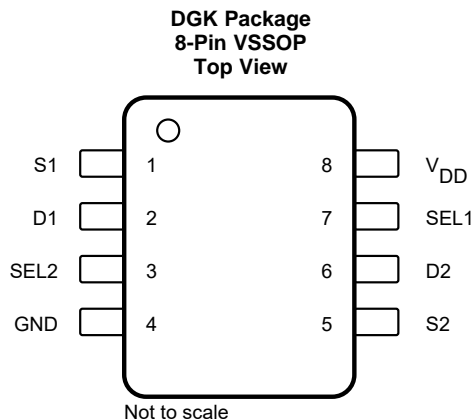
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• 将文档从预告信息 更改为生产数据	1
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5 Device Comparison Table

PRODUCT	DESCRIPTION
TMUX1121	Low-Leakage-Current, 1:1 (SPST), 2-Channel Precision Switches (Active High)
TMUX1122	Low-Leakage-Current, 1:1 (SPST), 2-Channel Precision Switches (Active Low)
TMUX1123	Low-Leakage-Current, 1:1 (SPST), 2-Channel Precision Switches (Active High + Active Low)

6 Pin Configuration and Functions



Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION ⁽²⁾
NAME	NO.		
S1	1	I/O	Source pin 1. Can be an input or output.
D1	2	I/O	Drain pin 1. Can be an input or output.
SEL2	3	I	Logic control select pin 2. Controls channel 2 state as shown in Truth Tables .
GND	4	P	Ground (0 V) reference
S2	5	I/O	Source pin 2. Can be an input or output.
D2	6	I/O	Drain pin 2. Can be an input or output.
SEL1	7	I	Logic control select pin 1. Controls channel 1 state as shown in Truth Tables .
V _{DD}	8	P	Positive power supply. This pin is the most positive power-supply potential. For reliable operation, connect a decoupling capacitor ranging from 0.1 μF to 10 μF between V _{DD} and GND.

(1) I = input, O = output, I/O = input and output, P = power

(2) Refer to [Device Functional Modes](#) for what to do with unused pins

7 Specifications

7.1 Absolute Maximum Ratings

 over operating free-air temperature range (unless otherwise noted) ⁽¹⁾ ⁽²⁾ ⁽³⁾

		MIN	MAX	UNIT
V _{DD}	Supply voltage	-0.5	6	V
V _{SEL}	Logic control input pin voltage (SELx)	-0.5	6	V
I _{SEL}	Logic control input pin current (SELx)	-30	30	mA
V _S or V _D	Source or drain voltage (Sx, Dx)	-0.5	V _{DD} +0.5	V
I _S or I _D (CONT)	Source or drain continuous current (Sx, Dx)	-30	30	mA
T _{stg}	Storage temperature	-65	150	°C
T _J	Junction temperature		150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- (3) All voltages are with respect to ground, unless otherwise specified.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±750	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{DD}	Positive power supply voltage	1.08		5.5	V
V _S or V _D	Signal path input/output voltage (source or drain pins: Sx, Dx)	0		V _{DD}	V
V _{SEL}	Logic control input pin voltage (SELx)	0		5.5	V
I _S or I _D	Signal path continuous current (source or drain pins: Sx, Dx)	-30		30	mA
T _A	Ambient temperature	-40		125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TMUX1121 / TMUX1122 / TMUX1123	UNIT
		DGK (VSSOP)	
		8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	205.5	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	91.7	°C/W
R _{θJB}	Junction-to-board thermal resistance	127.0	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	25.9	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	125.3	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics ($V_{DD} = 5\text{ V} \pm 10\%$)

at $T_A = 25^\circ\text{C}$, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	1.9		4	Ω
			–40°C to +85°C			4.5	Ω
			–40°C to +125°C			4.9	Ω
ΔR_{ON}	On-resistance matching between channels	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	0.13			Ω
			–40°C to +85°C			0.4	Ω
			–40°C to +125°C			0.5	Ω
$R_{ON\ FLAT}$	On-resistance flatness	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	0.85			Ω
			–40°C to +85°C			1.6	Ω
			–40°C to +125°C			1.6	Ω
$I_{S(OFF)}$	Source off leakage current ⁽¹⁾	$V_{DD} = 5\text{ V}$ Switch Off $V_D = 4.5\text{ V} / 1.5\text{ V}$ $V_S = 1.5\text{ V} / 4.5\text{ V}$ Refer to Off-leakage current	25°C	–0.08	± 0.003	0.08	nA
			–40°C to +85°C			0.3	nA
			–40°C to +125°C			0.9	nA
$I_{D(OFF)}$	Drain off leakage current ⁽¹⁾	$V_{DD} = 5\text{ V}$ Switch Off $V_D = 4.5\text{ V} / 1.5\text{ V}$ $V_S = 1.5\text{ V} / 4.5\text{ V}$ Refer to Off-leakage current	25°C	–0.08	± 0.003	0.08	nA
			–40°C to +85°C			0.3	nA
			–40°C to +125°C			0.9	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	$V_{DD} = 5\text{ V}$ Switch On $V_D = V_S = 4.5\text{ V} / 1.5\text{ V}$ Refer to On-leakage current	25°C	–0.1	± 0.003	0.1	nA
			–40°C to +85°C			0.35	nA
			–40°C to +125°C			2	nA
LOGIC INPUTS (SELx)							
V_{IH}	Input logic high		–40°C to +125°C	1.49		5.5	V
V_{IL}	Input logic low		–40°C to +125°C	0		0.87	V
I_{IH} I_{IL}	Input leakage current		25°C		± 0.005		μA
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			± 0.05	μA
C_{IN}	Logic input capacitance		25°C		1		pF
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic inputs = 0 V or 5.5 V	25°C		0.007		μA
			–40°C to +125°C			1	μA

(1) When V_S is 4.5 V, V_D is 1.5 V or when V_S is 1.5 V, V_D is 4.5 V.

Electrical Characteristics ($V_{DD} = 5\text{ V} \pm 10\%$) (continued)

 at $T_A = 25^\circ\text{C}$, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Transition time between channels	$V_S = 3\text{ V}$ $R_L = 200\ \Omega$, $C_L = 15\text{ pF}$ Refer to Transition time	25°C		12		ns
			–40°C to +85°C			17	ns
			–40°C to +125°C			18	ns
t_{OPEN} (BBM)	Break before make time (TMUX1123 Only)	$V_S = 3\text{ V}$ $R_L = 200\ \Omega$, $C_L = 15\text{ pF}$ Refer to Break-before-make	25°C		8		ns
			–40°C to +85°C		1		ns
			–40°C to +125°C		1		ns
Q_C	Charge Injection	$V_S = 1\text{ V}$ $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$ Refer to Charge injection	25°C		–1.5		pC
O_{ISO}	Off Isolation	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 1\text{ MHz}$ Refer to Off isolation	25°C		–62		dB
		$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 10\text{ MHz}$ Refer to Off isolation	25°C		–40		dB
X_{TALK}	Crosstalk	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 1\text{ MHz}$ Refer to Channel-to-Channel Crosstalk	25°C		–100		dB
		$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 10\text{ MHz}$ Refer to Channel-to-Channel Crosstalk	25°C		–90		dB
BW	Bandwidth	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ Refer to Bandwidth	25°C		300		MHz
C_{SOFF}	Source off capacitance	$f = 1\text{ MHz}$	25°C		6		pF
C_{DOFF}	Drain off capacitance	$f = 1\text{ MHz}$	25°C		10		pF
C_{SON} C_{DON}	On capacitance	$f = 1\text{ MHz}$	25°C		18		pF

7.6 Electrical Characteristics ($V_{DD} = 3.3\text{ V} \pm 10\%$)

at $T_A = 25^\circ\text{C}$, $V_{DD} = 3.3\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT	
ANALOG SWITCH								
R_{ON}	On-resistance	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	3.7	8.8		Ω	
			–40°C to +85°C			9.5	Ω	
			–40°C to +125°C			9.8	Ω	
ΔR_{ON}	On-resistance matching between channels	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	0.13			Ω	
			–40°C to +85°C			0.4	Ω	
			–40°C to +125°C			0.5	Ω	
$R_{ON\text{ FLAT}}$	On-resistance flatness	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	1.9			Ω	
			–40°C to +85°C			2	Ω	
			–40°C to +125°C			2.2	Ω	
$I_{S(OFF)}$	Source off leakage current ⁽¹⁾	$V_{DD} = 3.3\text{ V}$ Switch Off $V_D = 3\text{ V} / 1\text{ V}$ $V_S = 1\text{ V} / 3\text{ V}$ Refer to Off-leakage current	25°C	–0.05	± 0.001	0.05	nA	
			–40°C to +85°C			–0.2	0.2	nA
			–40°C to +125°C			–0.9	0.9	nA
$I_{D(OFF)}$	Drain off leakage current ⁽¹⁾	$V_{DD} = 3.3\text{ V}$ Switch Off $V_D = 3\text{ V} / 1\text{ V}$ $V_S = 1\text{ V} / 3\text{ V}$ Refer to Off-leakage current	25°C	–0.05	± 0.001	0.05	nA	
			–40°C to +85°C			–0.2	0.2	nA
			–40°C to +125°C			–0.9	0.9	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	$V_{DD} = 3.3\text{ V}$ Switch On $V_D = V_S = 3\text{ V} / 1\text{ V}$ Refer to On-leakage current	25°C	–0.1	± 0.003	0.1	nA	
			–40°C to +85°C			–0.35	0.35	nA
			–40°C to +125°C			–2	2	nA
LOGIC INPUTS (SELx)								
V_{IH}	Input logic high		–40°C to +125°C	1.35		5.5	V	
V_{IL}	Input logic low		–40°C to +125°C	0		0.8	V	
I_{IH} I_{IL}	Input leakage current		25°C	± 0.005			μA	
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			± 0.05	μA	
C_{IN}	Logic input capacitance		25°C		1		pF	
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF	
POWER SUPPLY								
I_{DD}	V_{DD} supply current	Logic inputs = 0 V or 5.5 V	25°C	0.004			μA	
			–40°C to +125°C			1	μA	

(1) When V_S is 3 V, V_D is 1 V or when V_S is 1 V, V_D is 3 V.

Electrical Characteristics ($V_{DD} = 3.3 \text{ V} \pm 10 \%$) (continued)

 at $T_A = 25^\circ\text{C}$, $V_{DD} = 3.3 \text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Transition time between channels	$V_S = 2 \text{ V}$ $R_L = 200 \Omega$, $C_L = 15 \text{ pF}$ Refer to Transition time	25°C	14			ns
			–40°C to +85°C			20	ns
			–40°C to +125°C			22	ns
t_{OPEN} (BBM)	Break before make time (TMUX1123 Only)	$V_S = 2 \text{ V}$ $R_L = 200 \Omega$, $C_L = 15 \text{ pF}$ Refer to Break-before-make	25°C	9			ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	$V_S = 1 \text{ V}$ $R_S = 0 \Omega$, $C_L = 1 \text{ nF}$ Refer to Charge injection	25°C		–1.5		pC
O_{ISO}	Off Isolation	$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$ $f = 1 \text{ MHz}$ Refer to Off isolation	25°C		–62		dB
		$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$ $f = 10 \text{ MHz}$ Refer to Off isolation	25°C		–40		dB
X_{TALK}	Crosstalk	$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$ $f = 1 \text{ MHz}$ Refer to Channel-to-Channel Crosstalk	25°C		–100		dB
		$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$ $f = 10 \text{ MHz}$ Refer to Channel-to-Channel Crosstalk	25°C		–90		dB
BW	Bandwidth	$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$ Refer to Bandwidth	25°C		300		MHz
C_{SOFF}	Source off capacitance	$f = 1 \text{ MHz}$	25°C		6		pF
C_{DOFF}	Drain off capacitance	$f = 1 \text{ MHz}$	25°C		10		pF
C_{SON} C_{DON}	On capacitance	$f = 1 \text{ MHz}$	25°C		18		pF

7.7 Electrical Characteristics ($V_{DD} = 1.8\text{ V} \pm 10\%$)

at $T_A = 25^\circ\text{C}$, $V_{DD} = 1.8\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	40			Ω
			–40°C to +85°C			80	Ω
			–40°C to +125°C			80	Ω
ΔR_{ON}	On-resistance matching between channels	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	0.4			Ω
			–40°C to +85°C			1.5	Ω
			–40°C to +125°C			1.5	Ω
$I_{S(OFF)}$	Source off leakage current ⁽¹⁾	$V_{DD} = 1.98\text{ V}$ Switch Off $V_D = 1.62\text{ V} / 1\text{ V}$ $V_S = 1\text{ V} / 1.62\text{ V}$ Refer to Off-leakage current	25°C	–0.05	± 0.001	0.05	nA
			–40°C to +85°C	–0.2		0.2	nA
			–40°C to +125°C	–0.9		0.9	nA
$I_{D(OFF)}$	Drain off leakage current ⁽¹⁾	$V_{DD} = 1.98\text{ V}$ Switch Off $V_D = 1.62\text{ V} / 1\text{ V}$ $V_S = 1\text{ V} / 1.62\text{ V}$ Refer to Off-leakage current	25°C	–0.05	± 0.001	0.05	nA
			–40°C to +85°C	–0.2		0.2	nA
			–40°C to +125°C	–0.9		0.9	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	$V_{DD} = 1.98\text{ V}$ Switch On $V_D = V_S = 1.62\text{ V} / 1\text{ V}$ Refer to On-leakage current	25°C	–0.1	± 0.003	0.1	nA
			–40°C to +85°C	–0.35		0.35	nA
			–40°C to +125°C	–2		2	nA
LOGIC INPUTS (SELx)							
V_{IH}	Input logic high		–40°C to +125°C	1.07		5.5	V
V_{IL}	Input logic low		–40°C to +125°C	0		0.68	V
I_{IH} I_{IL}	Input leakage current		25°C	± 0.005			μA
			–40°C to +125°C			± 0.05	μA
C_{IN}	Logic input capacitance		25°C	1			pF
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic inputs = 0 V or 5.5 V	25°C	0.001			μA
			–40°C to +125°C			0.85	μA

(1) When V_S is 1.62 V, V_D is 1 V or when V_S is 1 V, V_D is 1.62 V.

Electrical Characteristics ($V_{DD} = 1.8\text{ V} \pm 10\%$) (continued)

 at $T_A = 25^\circ\text{C}$, $V_{DD} = 1.8\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Transition time between channels	$V_S = 1\text{ V}$ $R_L = 200\ \Omega$, $C_L = 15\text{ pF}$ Refer to Transition time	25°C	25			ns
			–40°C to +85°C			44	ns
			–40°C to +125°C			44	ns
t_{OPEN} (BBM)	Break before make time (TMUX1123 Only)	$V_S = 1\text{ V}$ $R_L = 200\ \Omega$, $C_L = 15\text{ pF}$ Refer to Break-before-make	25°C	17			ns
			–40°C to +85°C		1		ns
			–40°C to +125°C		1		ns
Q_C	Charge Injection	$V_S = 1\text{ V}$ $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$ Refer to Charge injection	25°C		–0.5		pC
O_{ISO}	Off Isolation	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 1\text{ MHz}$ Refer to Off isolation	25°C		–62		dB
		$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 10\text{ MHz}$ Refer to Off isolation	25°C		–40		dB
X_{TALK}	Crosstalk	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 1\text{ MHz}$ Refer to Channel-to-Channel Crosstalk	25°C		–100		dB
		$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 10\text{ MHz}$ Refer to Channel-to-Channel Crosstalk	25°C		–90		dB
BW	Bandwidth	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ Refer to Bandwidth	25°C		300		MHz
C_{SOFF}	Source off capacitance	$f = 1\text{ MHz}$	25°C		6		pF
C_{DOFF}	Drain off capacitance	$f = 1\text{ MHz}$	25°C		10		pF
C_{SON} C_{DON}	On capacitance	$f = 1\text{ MHz}$	25°C		18		pF

7.8 Electrical Characteristics ($V_{DD} = 1.2\text{ V} \pm 10\%$)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	70			Ω
			-40°C to +85°C			105	Ω
			-40°C to +125°C			105	Ω
ΔR_{ON}	On-resistance matching between channels	$V_S = 0\text{ V to }V_{DD}$ $I_{SD} = 10\text{ mA}$ Refer to On-resistance	25°C	0.4			Ω
			-40°C to +85°C			1.5	Ω
			-40°C to +125°C			1.5	Ω
$I_{S(OFF)}$	Source off leakage current ⁽¹⁾	$V_{DD} = 1.32\text{ V}$ Switch Off $V_D = 1\text{ V} / 0.8\text{ V}$ $V_S = 0.8\text{ V} / 1\text{ V}$ Refer to Off-leakage current	25°C	-0.05	± 0.001	0.05	nA
			-40°C to +85°C	-0.2		0.2	nA
			-40°C to +125°C	-0.9		0.9	nA
$I_{D(OFF)}$	Drain off leakage current ⁽¹⁾	$V_{DD} = 1.32\text{ V}$ Switch Off $V_D = 1\text{ V} / 0.8\text{ V}$ $V_S = 0.8\text{ V} / 1\text{ V}$ Refer to Off-leakage current	25°C	-0.05	± 0.001	0.05	nA
			-40°C to +85°C	-0.2		0.2	nA
			-40°C to +125°C	-0.9		0.9	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	$V_{DD} = 1.32\text{ V}$ Switch On $V_D = V_S = 1\text{ V} / 0.8\text{ V}$ Refer to On-leakage current	25°C	-0.1	± 0.003	0.1	nA
			-40°C to +85°C	-0.35		0.35	nA
			-40°C to +125°C	-2		2	nA
LOGIC INPUTS (SELx)							
V_{IH}	Input logic high		-40°C to +125°C	0.96		5.5	V
V_{IL}	Input logic low		-40°C to +125°C	0		0.36	V
I_{IH} I_{IL}	Input leakage current		25°C	± 0.005			μA
			-40°C to +125°C			± 0.05	μA
C_{IN}	Logic input capacitance		25°C	1			pF
C_{IN}	Logic input capacitance		-40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic inputs = 0 V or 5.5 V	25°C	0.001			μA
			-40°C to +125°C			0.7	μA

(1) When V_S is 1 V, V_D is 0.8 V or when V_S is 0.8 V, V_D is 1 V.

Electrical Characteristics ($V_{DD} = 1.2\text{ V} \pm 10\%$) (continued)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Transition time between channels	$V_S = 1\text{ V}$ $R_L = 200\ \Omega$, $C_L = 15\text{ pF}$ Refer to Transition time	25°C	55			ns
			–40°C to +85°C		190		ns
			–40°C to +125°C		190		ns
t_{OPEN} (BBM)	Break before make time (TMUX1123 Only)	$V_S = 1\text{ V}$ $R_L = 200\ \Omega$, $C_L = 15\text{ pF}$ Refer to Break-before-make	25°C	28			ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	$V_S = 1\text{ V}$ $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$ Refer to Charge injection	25°C		–0.5		pC
O_{ISO}	Off Isolation	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 1\text{ MHz}$ Refer to Off isolation	25°C		–62		dB
			$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 10\text{ MHz}$ Refer to Off isolation	25°C		–40	
X_{TALK}	Crosstalk	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 1\text{ MHz}$ Refer to Channel-to-Channel Crosstalk	25°C		–100		dB
			$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ $f = 10\text{ MHz}$ Refer to Channel-to-Channel Crosstalk	25°C		–90	
BW	Bandwidth	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$ Refer to Bandwidth	25°C		300		MHz
C_{SOFF}	Source off capacitance	$f = 1\text{ MHz}$	25°C		6		pF
C_{DOFF}	Drain off capacitance	$f = 1\text{ MHz}$	25°C		10		pF
C_{SON} C_{DON}	On capacitance	$f = 1\text{ MHz}$	25°C		18		pF

7.9 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

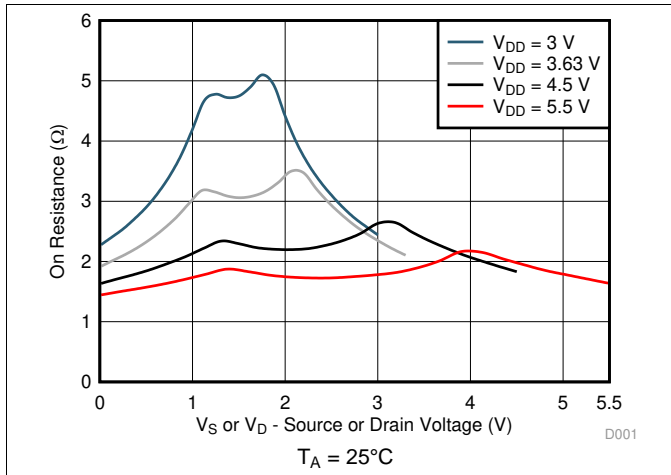


图 1. On-Resistance vs Source or Drain Voltage

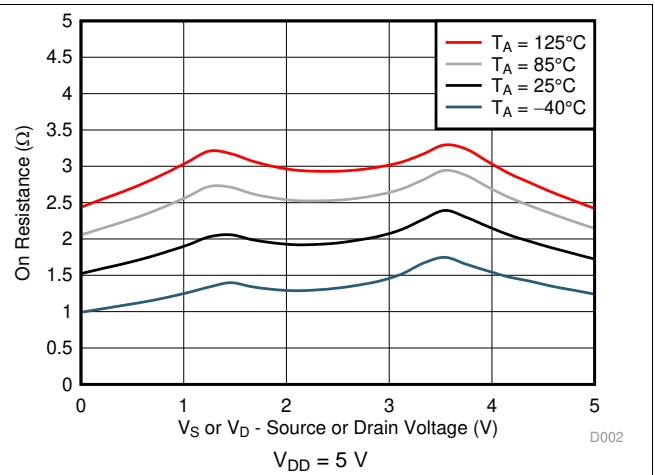


图 2. On-Resistance vs Temperature

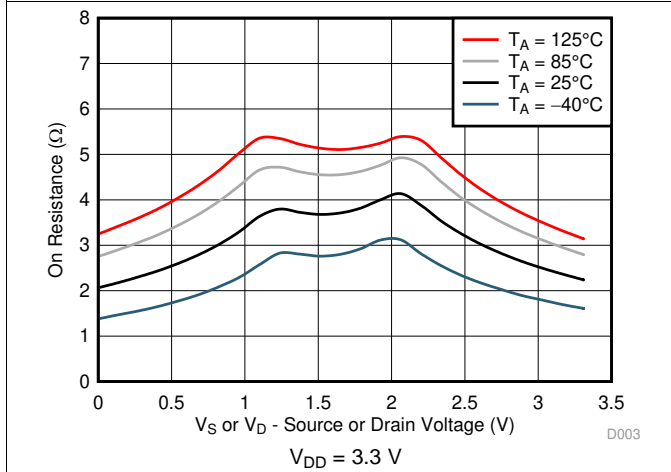


图 3. On-Resistance vs Temperature

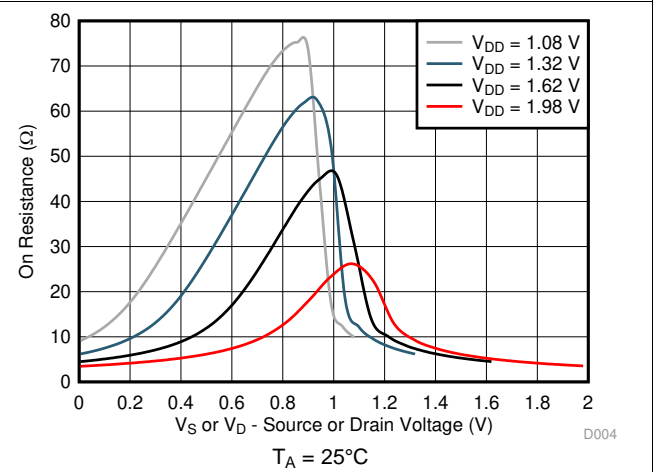


图 4. On-Resistance vs Source or Drain Voltage

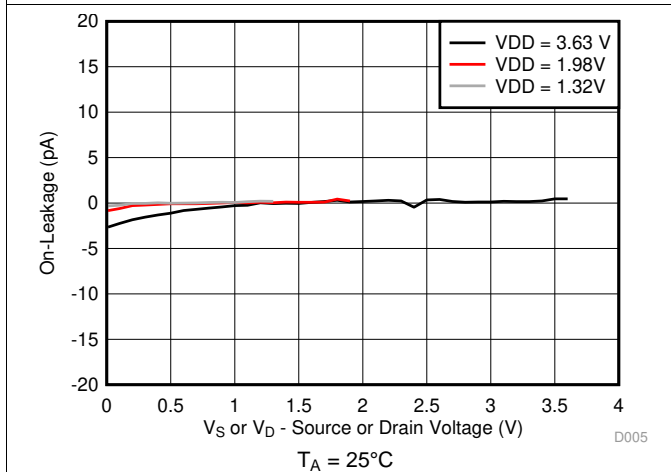


图 5. On-Leakage vs Source or Drain Voltage

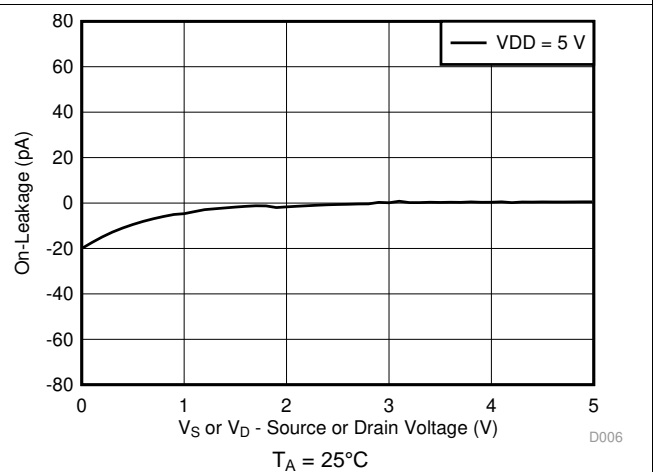


图 6. On-Leakage vs Source or Drain Voltage

Typical Characteristics (接下页)

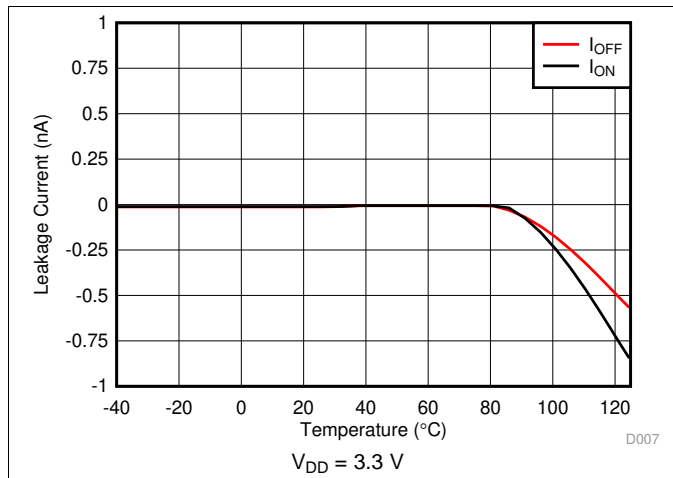


图 7. Leakage Current vs Temperature

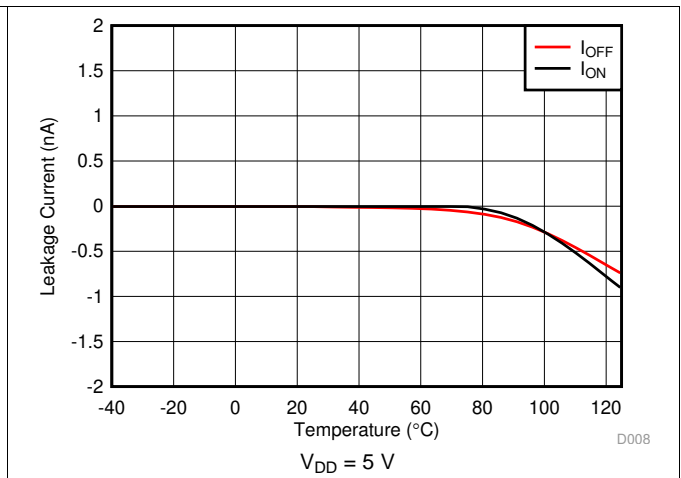


图 8. Leakage Current vs Temperature

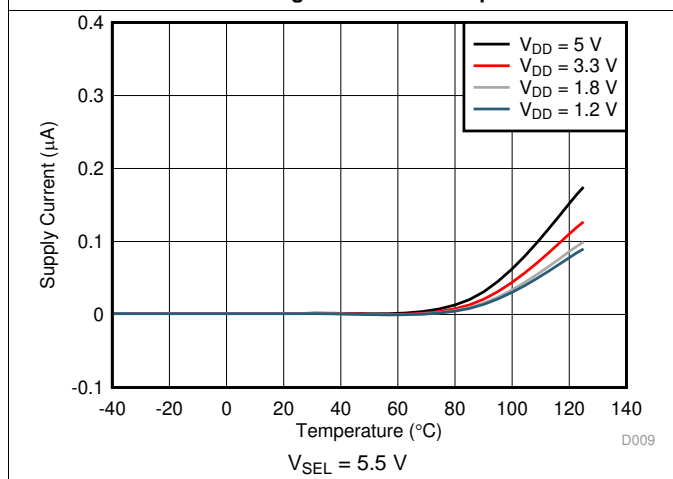


图 9. Supply Current vs Temperature

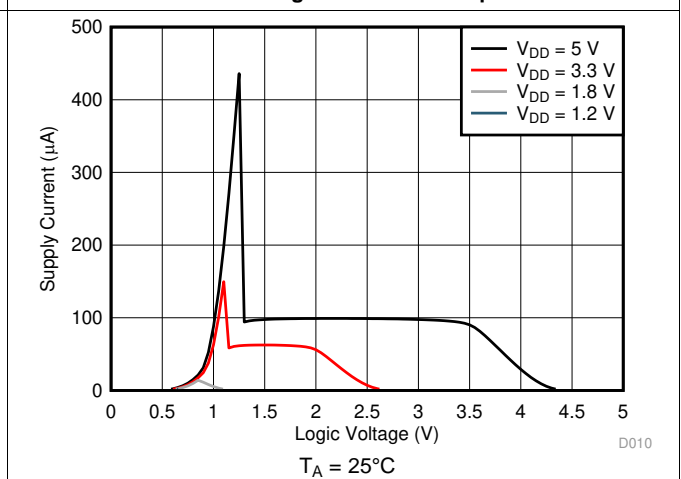


图 10. Supply Current vs Logic Voltage

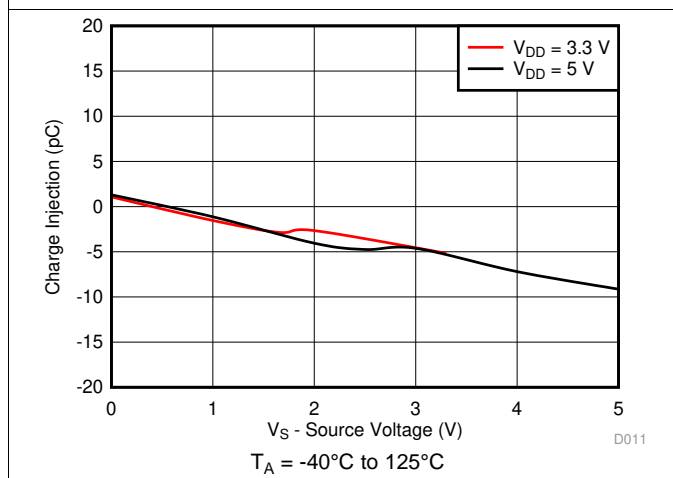


图 11. Charge Injection vs Source Voltage

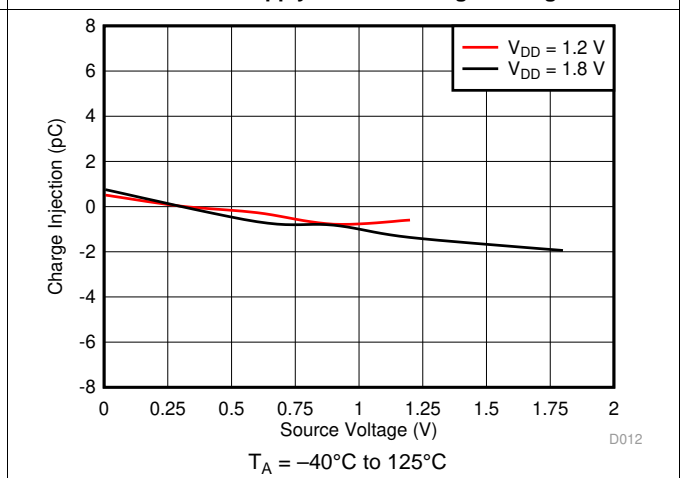


图 12. Charge Injection vs Source Voltage

Typical Characteristics (接下页)

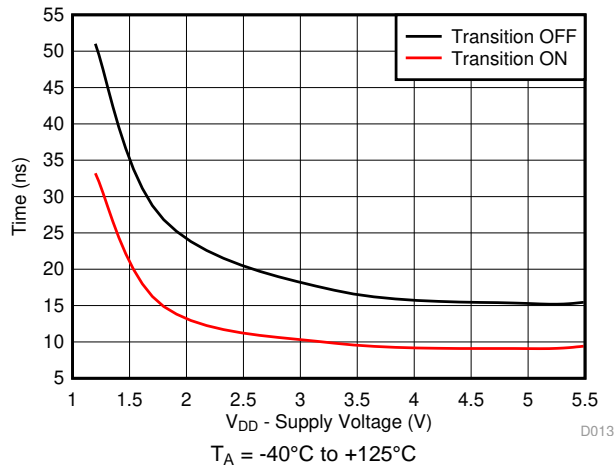


图 13. Output $T_{\text{TRANSITION}}$ vs Supply Voltage

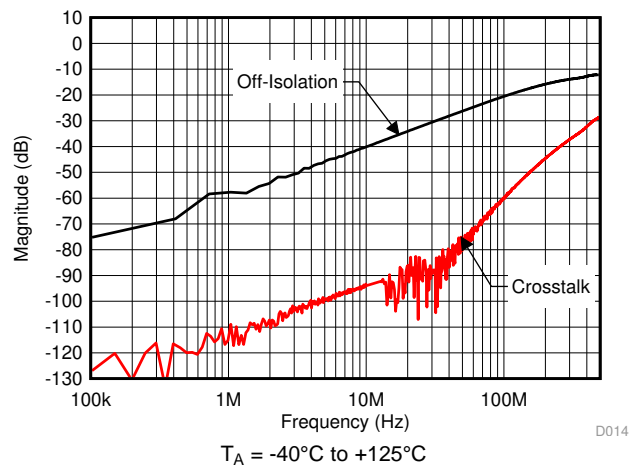


图 14. Off-Isolation vs Frequency

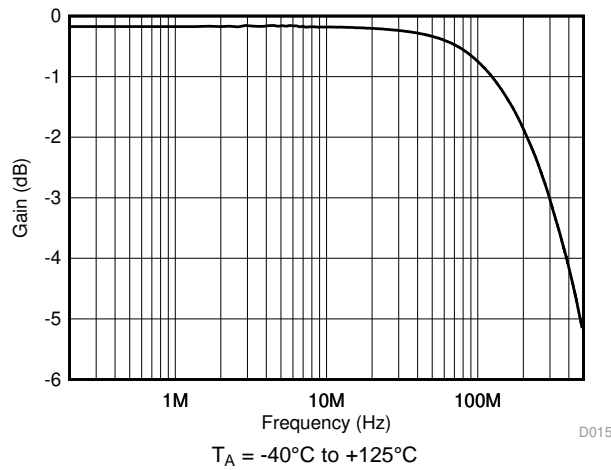


图 15. On Response vs Frequency

8 Parameter Measurement Information

8.1 On-resistance

The on-resistance of a device is the ohmic resistance between the source (Sx) and drain (Dx) pins of the device. The on-resistance varies with input voltage and supply voltage. The symbol R_{ON} is used to denote on-resistance. The measurement setup used to measure R_{ON} is shown in [图 16](#). Voltage (V) and current (I_{SD}) are measured using this setup, and R_{ON} is computed with $R_{ON} = V / I_{SD}$:

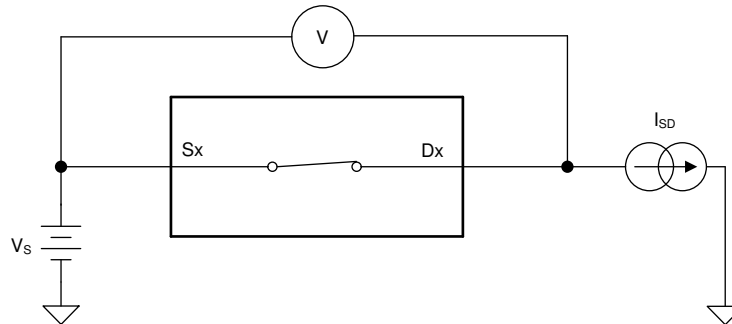


图 16. On-Resistance measurement setup

8.2 Off-leakage current

There are two types of leakage currents associated with a switch during the off state:

1. Source off-leakage current
2. Drain off-leakage current

Source leakage current is defined as the leakage current flowing into or out of the source pin when the switch is off. This current is denoted by the symbol $I_{S(OFF)}$.

Drain leakage current is defined as the leakage current flowing into or out of the drain pin when the switch is off. This current is denoted by the symbol $I_{D(OFF)}$.

The setup used to measure both off-leakage currents is shown in [图 17](#).

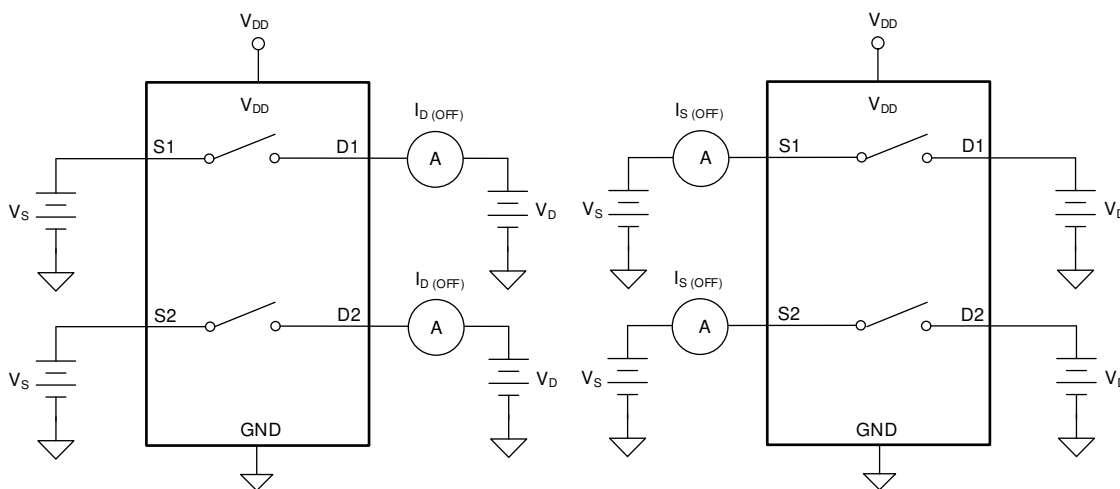


图 17. Off-leakage measurement setup

8.3 On-leakage current

Source on-leakage current is defined as the leakage current flowing into or out of the source pin when the switch is on. This current is denoted by the symbol $I_{S(ON)}$.

Drain on-leakage current is defined as the leakage current flowing into or out of the drain pin when the switch is on. This current is denoted by the symbol $I_{D(ON)}$.

Either the source pin or drain pin is left floating during the measurement. 图 18 shows the circuit used for measuring the on-leakage current, denoted by $I_{S(ON)}$ or $I_{D(ON)}$.

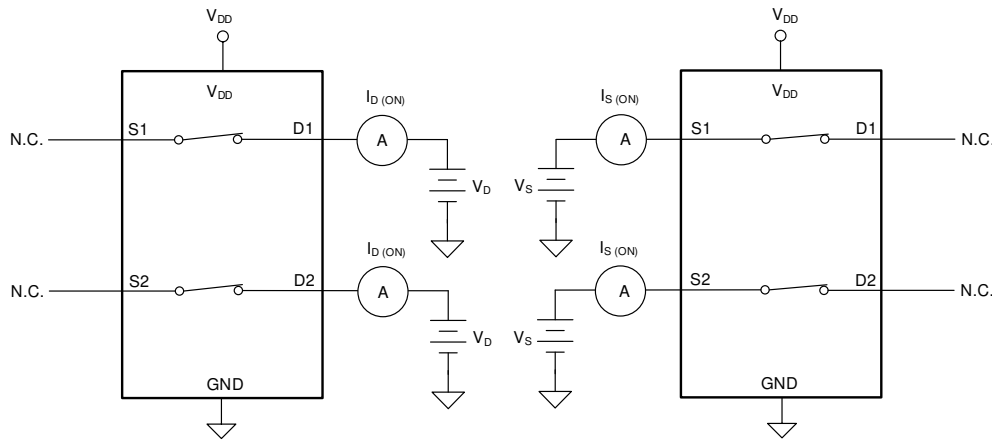


图 18. On-leakage measurement setup

8.4 Transition time

Transition time is defined as the time taken by the output of the device to rise or fall 10% after the address signal has risen or fallen past the logic threshold. The 10% transition measurement is utilized to provide the timing of the device. System level timing can then account for the time constant added from the load resistance and load capacitance. 图 19 shows the setup used to measure transition time, denoted by the symbol $t_{TRANSITION}$.

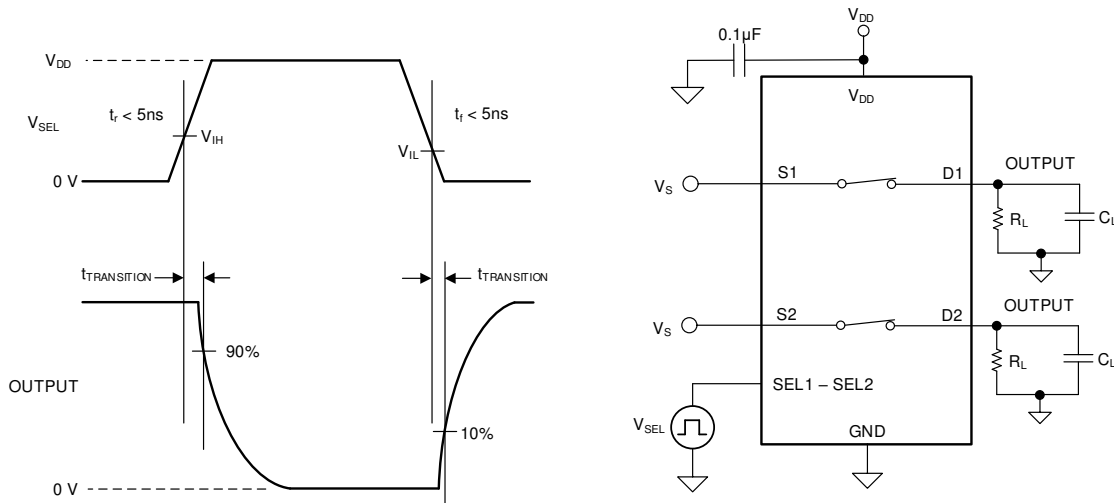


图 19. Transition-time measurement setup

8.5 Break-before-make

The TMUX1123 has break-before-make delay which allows the device to be used in cross-point switching application. The output first breaks from the on-state switch before making the connection with the next on-state switch. The time delay between the *break* and the *make* is known as break-before-make delay. shows the setup used to measure break-before-make delay, denoted by the symbol $t_{OPEN(BBM)}$.

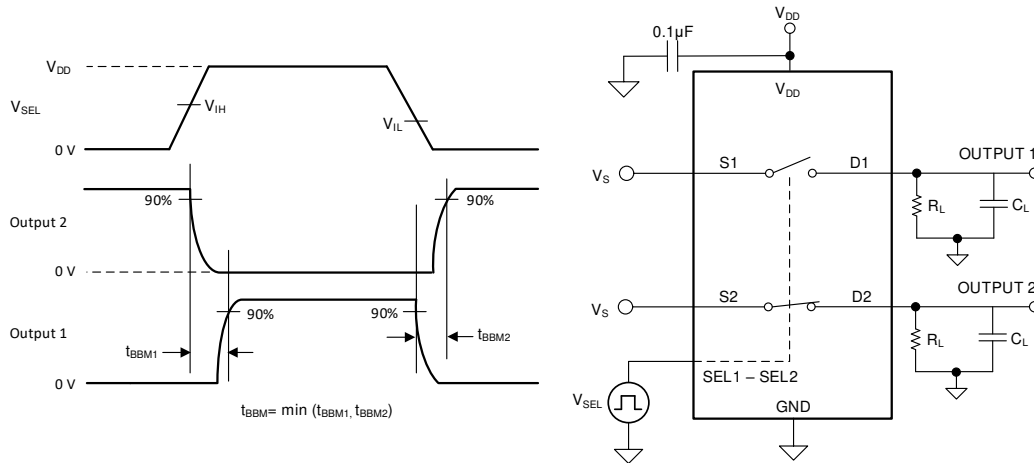


图 20. Break-before-make delay measurement setup

8.6 Charge injection

The TMUX112x devices have a transmission-gate topology. Any mismatch in capacitance between the NMOS and PMOS transistors results in a charge injected into the drain or source during the falling or rising edge of the gate signal. The amount of charge injected into the source or drain of the device is known as charge injection, and is denoted by the symbol Q_C . shows the setup used to measure charge injection from source (S_x) to drain (D_x).

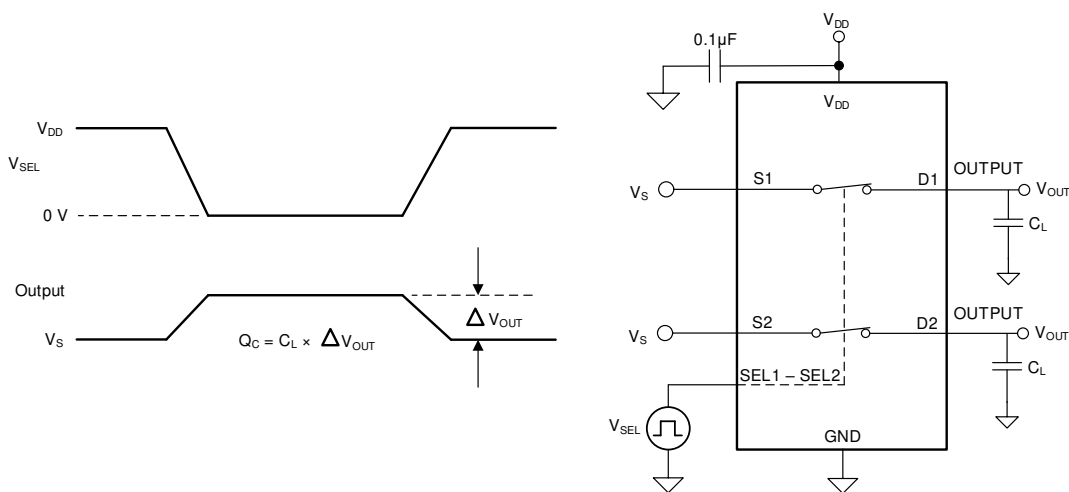


图 21. Charge-injection measurement setup

8.7 Off isolation

Off isolation is defined as the ratio of the signal at the drain pin (Dx) of the device when a signal is applied to the source pin (Sx) of an off-channel. The characteristic impedance, Z_0 , for the measurement is $50\ \Omega$. [Figure 22](#) shows the setup used to measure off isolation. Use off isolation equation to compute off isolation.

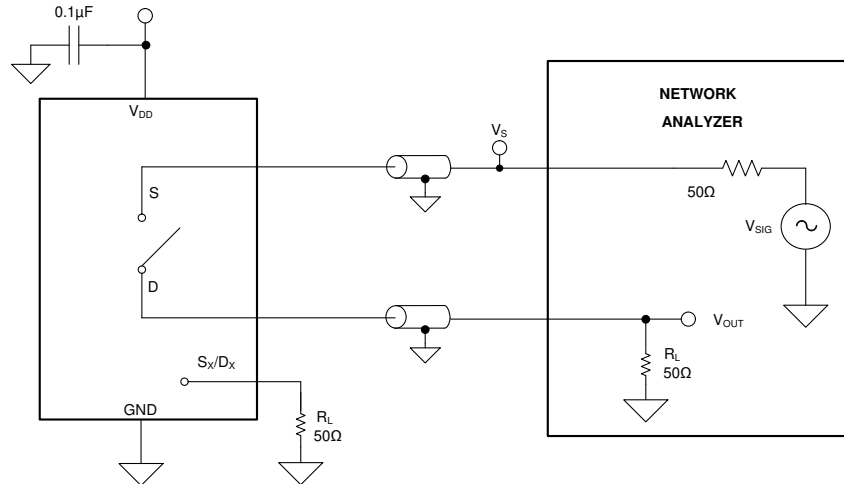


图 22. Off isolation measurement setup

$$\text{Off Isolation} = 20 \cdot \text{Log} \left(\frac{V_{\text{OUT}}}{V_{\text{S}}} \right) \quad (1)$$

8.8 Channel-to-Channel Crosstalk

Crosstalk is defined as the ratio of the signal at the drain pin (Dx) of a different channel, when a signal is applied at the source pin (Sx) of an on-channel. The characteristic impedance, Z_0 , for the measurement is $50\ \Omega$. [Figure 23](#) shows the setup used to measure, and the equation used to compute crosstalk.

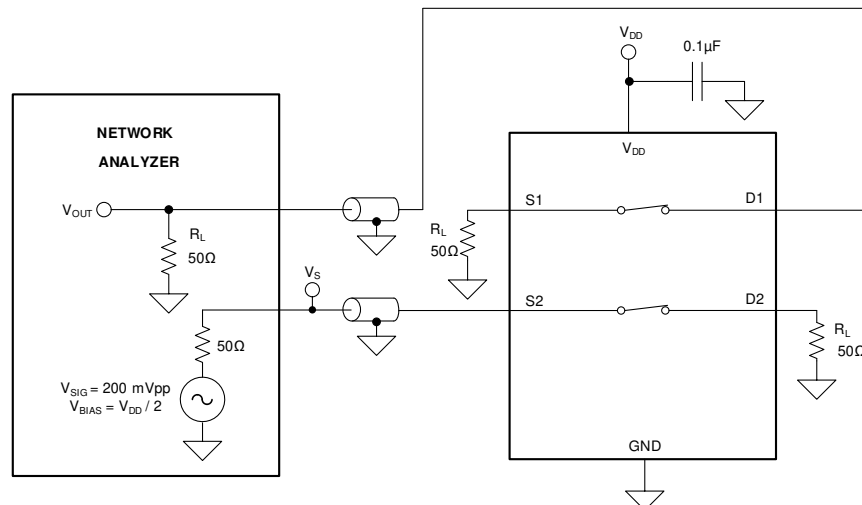


图 23. Channel-to-Channel Crosstalk Measurement Setup

$$\text{Channel-to-Channel Crosstalk} = 20 \cdot \text{Log} \left(\frac{V_{\text{OUT}}}{V_{\text{S}}} \right) \quad (2)$$

8.9 Bandwidth

Bandwidth is defined as the range of frequencies that are attenuated by less than 3 dB when the input is applied to the source pin (Sx) of an on-channel, and the output is measured at the drain pin (Dx) of the device. The characteristic impedance, Z_0 , for the measurement is $50\ \Omega$. 图 24 shows the setup used to measure bandwidth.

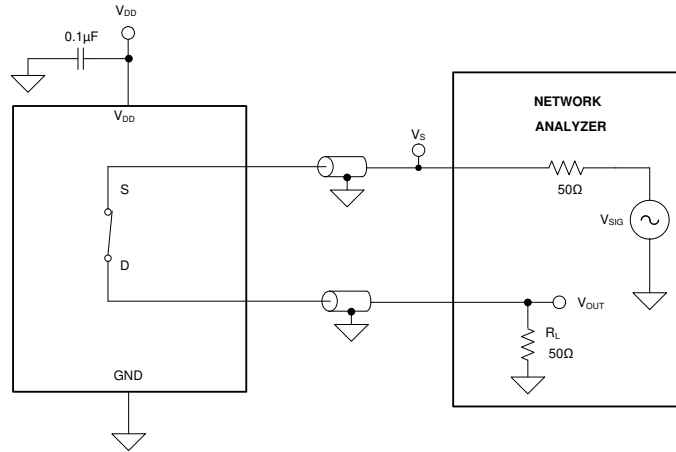


图 24. Bandwidth measurement setup

9 Detailed Description

9.1 Overview

The TMUX1121, TMUX1122, and TMUX1123 are 1:1 (SPST), 2-Channel switches. The devices have two independently selectable single-pole, single-throw switches that are turned-on or turned-off based on the state of the corresponding select pin.

9.2 Functional Block Diagram

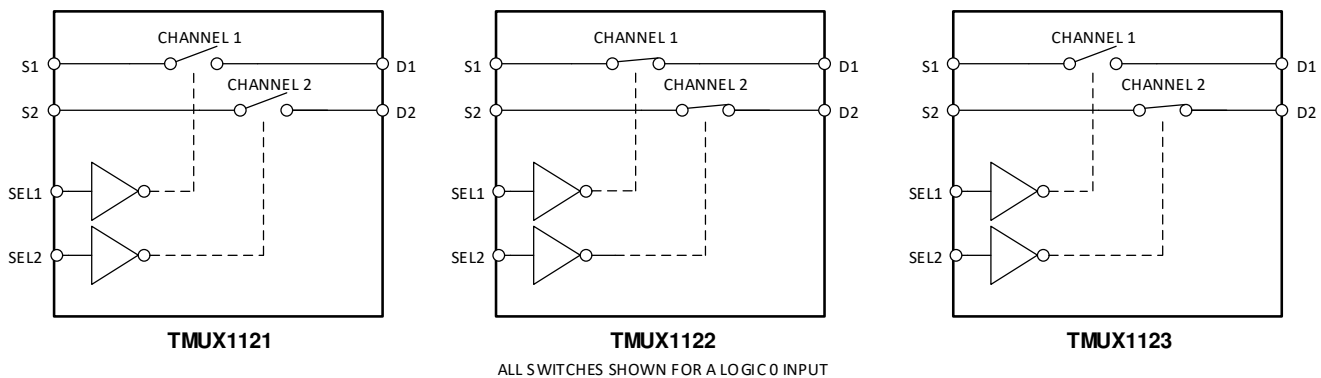


图 25. TMUX112x Functional Block Diagram

9.3 Feature Description

9.3.1 Bidirectional operation

The TMUX112x conducts equally well from source (S_x) to drain (D_x) or from drain (D_x) to source (S_x). Each channel has very similar characteristics in both directions and supports both analog and digital signals.

9.3.2 Rail to rail operation

The valid signal path input/output voltage for TMUX112x ranges from GND to V_{DD} .

9.3.3 1.8 V Logic compatible inputs

The TMUX112x devices have 1.8-V logic compatible control for all logic control inputs. The logic input thresholds scale with supply but still provide 1.8-V logic control when operating at 5.5 V supply voltage. 1.8-V logic level inputs allows the TMUX112x devices to interface with processors that have lower logic I/O rails and eliminates the need for an external translator, which saves both space and BOM cost. The current consumption of the TMUX112x devices increase when using 1.8V logic with higher supply voltage as shown in 图 10. For more information on 1.8 V logic implementations refer to [Simplifying Design with 1.8 V logic Muxes and Switches](#)

9.3.4 Fail-safe logic

The TMUX112x supports Fail-Safe Logic on the control input pins (EN, A0, A1) allowing for operation up to 5.5 V, regardless of the state of the supply pin. This feature allows voltages on the control pins to be applied before the supply pin, protecting the device from potential damage. Fail-Safe Logic minimizes system complexity by removing the need for power supply sequencing on the logic control pins. For example, the Fail-Safe Logic feature allows the select pins of the TMUX112x to be ramped to 5.5 V while $V_{DD} = 0$ V. Additionally, the feature enables operation of the TMUX112x with $V_{DD} = 1.2$ V while allowing the select pins to interface with a logic level of another device up to 5.5 V.

Feature Description (接下页)

9.3.5 Ultra-low Leakage Current

The TMUX112x devices provide extremely low on-leakage and off-leakage currents. The TMUX112x devices are capable of switching signals from high source-impedance inputs into a high input-impedance op amp with minimal offset error because of the ultra-low leakage currents. 图 26 shows typical leakage currents of the TMUX112x devices versus temperature at $V_{DD} = 5V$.

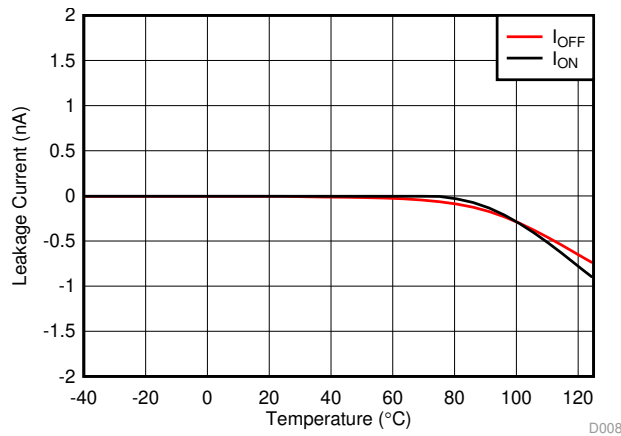


图 26. Leakage Current vs Temperature

9.3.6 Ultra-low Charge Injection

The TMUX112x devices have a transmission gate topology, as shown in 图 27. Any mismatch in the stray capacitance associated with the NMOS and PMOS causes an output level change whenever the switch is opened or closed.

The TMUX112x devices have special charge-injection cancellation circuitry that reduces the source-to-drain charge injection to -1.5 pC at $V_S = 1 \text{ V}$ as shown in 图 28.

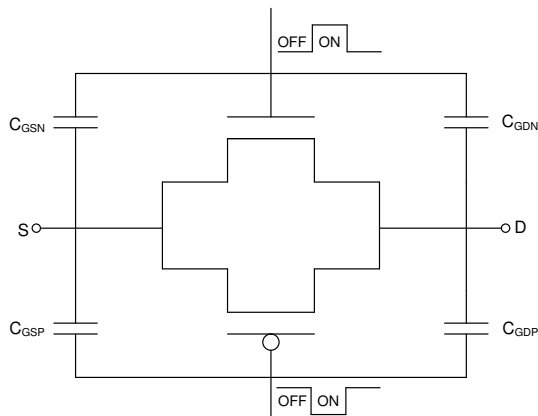


图 27. Transmission Gate Topology

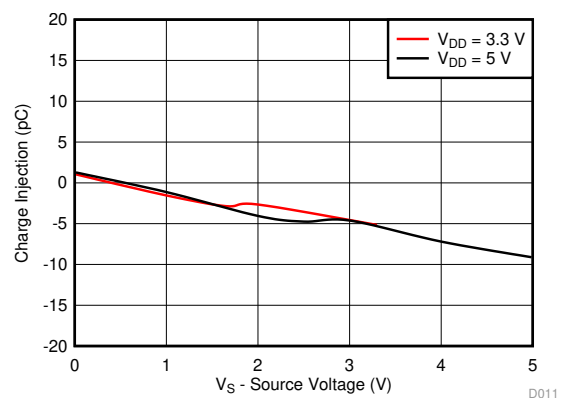


图 28. Charge Injection vs Source Voltage

9.4 Device Functional Modes

The TMUX112x devices have two independently selectable single-pole, single-throw switches that are turned-on or turned-off based on the state of the corresponding select pin. The control pins can be as high as 5.5 V.

The TMUX112x devices can be operated without any external components except for the supply decoupling capacitors. Unused logic control pins should be tied to GND or V_{DD} in order to ensure the device does not consume additional current as highlighted in *Implications of Slow or Floating CMOS Inputs*. Unused signal path inputs (Sx or Dx) should be connected to GND.

9.4.1 Truth Tables

表 1, 表 2, and 表 3 show the truth tables for the TMUX1121, TMUX1122, and TMUX1123, respectively.

表 1. TMUX1121 Truth table⁽¹⁾

SEL1	SEL2	CHANNEL STATE
0	X	Channel 1 OFF
1	X	Channel 1 ON
X	0	Channel 2 OFF
X	1	Channel 2 ON

(1) X denotes *don't care*.

表 2. TMUX1122 Truth table⁽¹⁾

SEL1	SEL2	CHANNEL STATE
0	X	Channel 1 ON
1	X	Channel 1 OFF
X	0	Channel 2 ON
X	1	Channel 2 OFF

(1) X denotes *don't care*.

表 3. TMUX1123 Truth table⁽¹⁾

SEL1	SEL2	CHANNEL STATE
0	X	Channel 1 OFF
1	X	Channel 1 ON
X	0	Channel 2 ON
X	1	Channel 2 OFF

(1) X denotes *don't care*.

10 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The TMUX11xx family offers ultra-low input/output leakage currents and low charge injection. These devices operate up to 5.5 V, and offer true rail-to-rail input and output of both analog and digital signals. The TMUX112x have a low on-capacitance which allows faster settling time when multiplexing inputs in the time domain. These features make the TMUX11xx devices a family of precision, high-performance switches and multiplexers for low-voltage applications.

10.2 Typical Application - Sample-and-Hold Circuit

One useful application to take advantage of the TMUX1121, TMUX1122, and TMUX1123 performance is the sample-and-hold circuit. A sample-and-hold circuit can be useful for an analog to digital converter (ADC) to sample a varying input voltage with improved reliability and stability. It can also be used to store the output samples from a single digital-to-analog converter (DAC) in a multi-output application. A simple sample-and-hold circuit can be realized using an analog switch such as the TMUX1121, TMUX1122, and TMUX1123 analog switches. 图 29 shows a single channel sample-and hold circuit using only 1 of 2 channels in the TMUX112x devices.

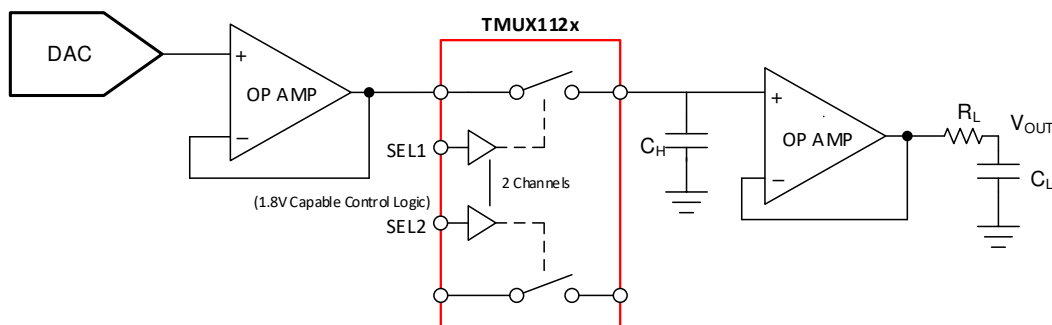


图 29. Single Channel Sample-and-Hold Circuit Example

An optional operational amplifier is used before the switch since buffered DACs typically have limitations in driving capacitive loads. The additional buffer stage is included following the DAC to prevent potential stability problems from driving a large capacitive load.

Ideally, the switch delivers only the input signals to the holding capacitors. However, when the switch gets toggled, some amount of charge also gets transferred to the switch output in the form of charge injection, resulting in a pedestal sampling error. The TMUX1121, TMUX1122, and TMUX1123 switches have excellent charge injection performance of only -1.5 pC, making them ideal choices for this implementation to minimize sampling error. The pedestal error voltage is indirectly related to the size of the capacitance on the output, for better precision a larger capacitor is required due to charge injection. Larger capacitance limits the system settling time which may not be acceptable in some applications. 图 30 shows a TMUX112x device configured for a 2-channel sample-and-hold circuit with pedestal error compensation.

Typical Application - Sample-and-Hold Circuit (接下页)

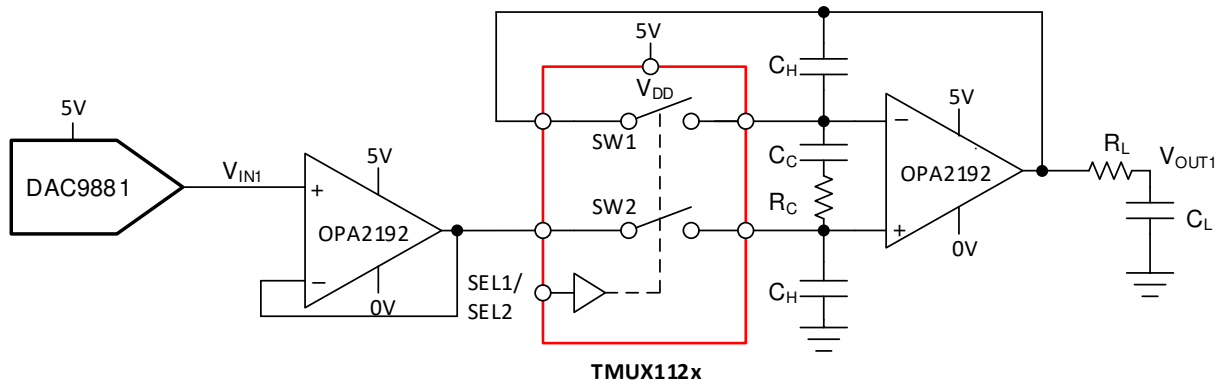


图 30. 2-Channel Sample-and-Hold Circuit with Pedestal Error Compensation

10.2.1 Design Requirements

The purpose of this precision design is to implement an optimized 2-output sample-and-hold circuit using a 2-channel 1:1 (SPST) switch. The sample and hold circuit needs to be capable of supporting high accuracy with minimized pedestal error and fast settling time..

10.2.2 Detailed Design Procedure

The TMUX1121, TMUX1122, or TMUX1123 switch is used in conjunction with the voltage holding capacitors (C_H) to implement the sample-and-hold circuit. The basic operation is:

1. When the switch (SW2) is closed, it samples the input voltage and charges the holding capacitors (C_H) to the input voltages values.
2. When the switch (SW2) is open, the holding capacitors (C_H) holds its previous value, maintaining stable voltage at the amplifier output (V_{OUT}).

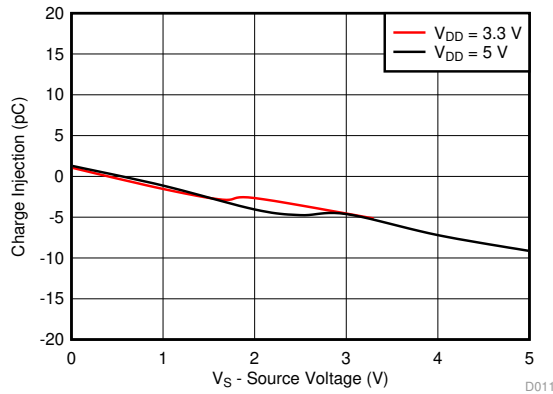
Due to switch and capacitor leakage current, as well as amplifier bias current, the voltage on the hold capacitors droops with time. The TMUX1121, TMUX1122, or TMUX1123 minimize the droops due to its ultra-low leakage performance. At 25°C, the TMUX1121, TMUX1122, and TMUX1123 have extremely low leakage current at 3 pA typical.

A second switch SW1 is also included to operate in parallel with SW2 to reduce pedestal error during switch toggling. Because both switches are driven at the same potential, they act as common-mode signal to the op-amp, thereby minimizing the charge injection effects caused by the switch toggling action. Compensation network consisting of R_C and C_C is also added to further reduce the pedestal error, while reducing the hold-time glitch and improving the settling time of the circuit. Refer to [Sample & Hold Glitch Reduction for Precision Outputs Reference Design](#) for more information on sample-and-hold circuits.

Typical Application - Sample-and-Hold Circuit (接下页)

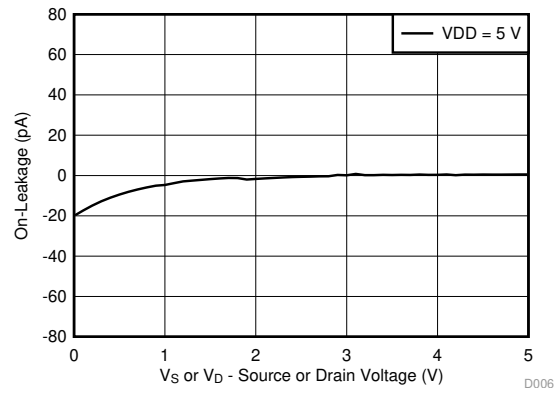
10.2.3 Application Curve

TMUX1121, TMUX1122, and TMUX1123 have excellent charge injection performance and ultra-low leakage current, making them ideal choices to minimize sampling error for the sample and hold application.



$T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$

图 31. Charge Injection vs Source Voltage



$V_{DD} = 5\text{ V}$

图 32. On-Leakage vs Source or Drain Voltage

10.3 Typical Application - Switched Gain Amplifier

Switches and multiplexers are commonly used in the feedback path of amplifier circuits to provide configurable gain control. By using various resistor values on each switch path the TMUX112x allows the system to have multiple gain settings. An external resistor, or utilizing 1 channel always being closed, ensures the amplifier isn't operating in an open loop configuration. A transimpedance amplifier (TIA) for photodiode inputs is a common circuit that requires gain control using a multi-channel switch to convert the output current of the photodiode into a voltage for the MCU or processor. The leakage current, capacitance, and charge injection performance of the TMUX112x are key specifications to evaluate when selecting a device for gain control.

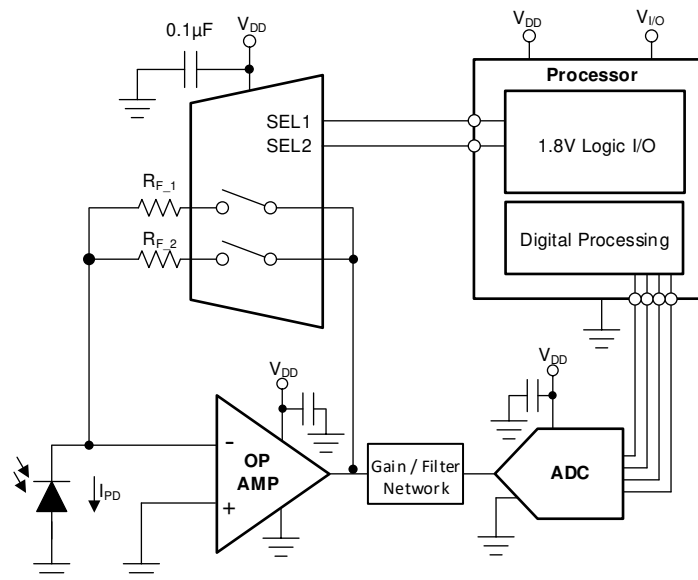


图 33. Switching Gain Settings of a TIA circuit

Typical Application - Switched Gain Amplifier (接下页)

10.3.1 Design Requirements

For this design example, use the parameters listed in 表 4.

表 4. Design parameters

PARAMETERS	VALUES
Supply (V_{DD})	3.3 V
Input / Output signal range	0 μ A to 10 μ A
Control logic thresholds	1.8 V compatible

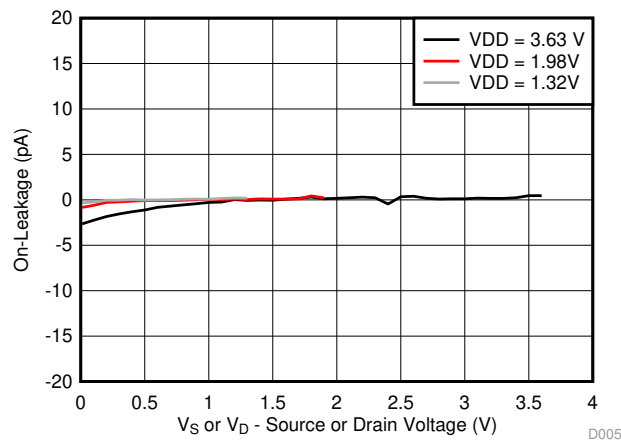
10.3.2 Detailed Design Procedure

The TMUX112x devices can be operated without any external components except for the supply decoupling capacitors. All inputs signals passing through the switch must fall within the recommend operating conditions of the TMUX112x including signal range and continuous current. For this design example, with a supply of 3.3 V, the signals can range from 0 V to 3.3 V when the device is powered. The max continuous current can be 30 mA.

Photodiodes commonly have a current output that ranges from a few hundred picoamps to tens of microamps based on the amount of light being absorbed. The TMUX112x have a typical On-leakage current of less than 10 pA which would lead to an accuracy well within 1% of a full scale 10 μ A signal. The low ON and OFF capacitance of the TMUX112x improves system stability by minimizing the total capacitance on the output of the amplifier. Lower capacitance leads to less overshoot and ringing in the system which can cause the amplifier circuit to go unstable if the phase margin is not at least 45°. Refer to [Improve Stability Issues with Low \$C_{ON}\$ Multiplexers](#) for more information on calculating the phase margin vs. percent overshoot.

10.3.3 Application Curve

The TMUX1121 is capable of switching signals from high source-impedance inputs into a high input-impedance op amp with minimal offset error because of the ultra-low leakage currents.



$$T_A = 25^\circ\text{C}$$

图 34. On-Leakage vs Source or Drain Voltage

11 Power Supply Recommendations

The TMUX112x operate across a wide supply range of 1.08 V to 5.5 V. Do not exceed the absolute maximum ratings because stresses beyond the listed ratings can cause permanent damage to the devices.

Power-supply bypassing improves noise margin and prevents switching noise propagation from the V_{DD} supply to other components. Good power-supply decoupling is important to achieve optimum performance. For improved supply noise immunity, use a supply decoupling capacitor ranging from 0.1 μF to 10 μF from V_{DD} to ground. Place the bypass capacitors as close to the power supply pins of the device as possible using low-impedance connections. TI recommends using multi-layer ceramic chip capacitors (MLCCs) that offer low equivalent series resistance (ESR) and inductance (ESL) characteristics for power-supply decoupling purposes. For very sensitive systems, or for systems in harsh noise environments, avoiding the use of vias for connecting the capacitors to the device pins may offer superior noise immunity. The use of multiple vias in parallel lowers the overall inductance and is beneficial for connections to ground planes.

12 Layout

12.1 Layout Guidelines

12.1.1 Layout Information

When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight, and therefore; some traces must turn corners. [图 35](#) shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

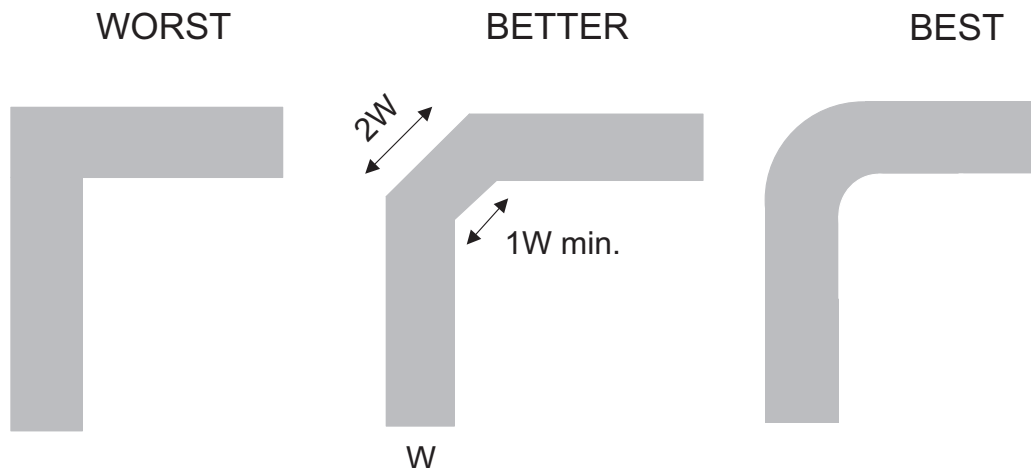


图 35. Trace example

Route high-speed signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points, through-hole pins are not recommended at high frequencies.

Layout Guidelines (接下页)

图 36 illustrates an example of a PCB layout with the TMUX112x. Some key considerations are:

- Decouple the V_{DD} pin with a 0.1- μF capacitor, placed as close to the pin as possible. Make sure that the capacitor voltage rating is sufficient for the V_{DD} supply.
- Keep the input lines as short as possible.
- Use a solid ground plane to help reduce electromagnetic interference (EMI) noise pickup.
- Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.

12.2 Layout Example

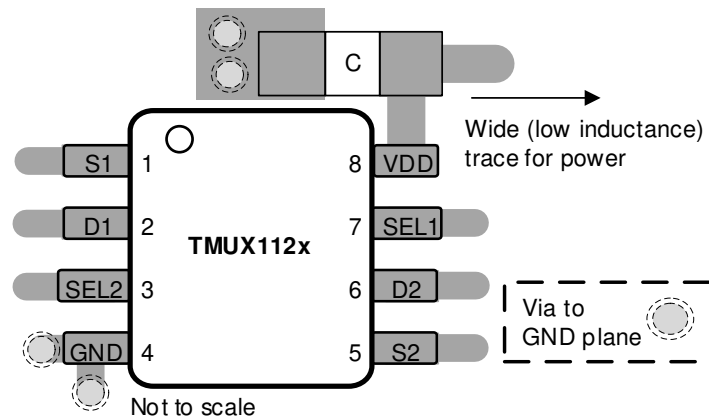


图 36. TMUX112x Layout example

13 器件和文档支持

13.1 文档支持

13.1.1 相关文档

- 德州仪器 (TI), 《[通过采样保持减少干扰实现精密输出的参考设计](#)》。
- 德州仪器 (TI), 《[真差分 4 x 2 多路复用器、模拟前端、同步采样 ADC 电路](#)》。
- 德州仪器 (TI), 《[使用低 CON 多路复用器改善稳定性问题](#)》。
- 德州仪器 (TI), 《[使用 1.8V 逻辑多路复用器和开关简化设计](#)》。
- 德州仪器 (TI), 《[利用关断保护信号开关消除电源排序](#)》。
- 德州仪器 (TI), 《[高电压模拟多路复用器的系统级保护](#)》。

13.2 相关链接

下表列出了快速访问链接。类别包括技术文档、支持和社区资源、工具和软件，以及立即订购快速访问。

表 5. 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持和社区
TMUX1121	单击此处	单击此处	单击此处	单击此处	单击此处
TMUX1122	单击此处	单击此处	单击此处	单击此处	单击此处
TMUX1123	单击此处	单击此处	单击此处	单击此处	单击此处

13.3 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。单击右上角的 [通知我](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

13.4 社区资源

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

13.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

14 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TMUX1121DGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	121	Samples
TMUX1122DGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	122	Samples
TMUX1123DGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	123	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TMUX1121DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TMUX1122DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TMUX1123DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TMUX1121DGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0
TMUX1122DGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0
TMUX1123DGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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